

TSV630, TSV630A, TSV631, TSV631A

Datasheet - production data

Rail-to-rail input/output, 60 µA, 880 kHz, 5 V CMOS operational amplifiers



Features

- Low offset voltage: 500 μV max (A version)
- Low power consumption: 60 µA typ at 5 V
- Low supply voltage: 1.5 V 5.5 V
- Gain bandwidth product: 880 kHz typ
- Unity gain stability
- Low power shutdown mode: 5 nA typ
- High output current: 63 mA at V_{CC} = 5 V
- Low input bias current: 1 pA typ
- Rail-to-rail input and output
- Extended temperature range: -40°C to +125°C
- Automotive qualification

Related products

- See the TSV52x series for higher merit factor (1.15 MHz for 45 µA)
- See the TSV61x (120 kHz for 9 μA) or the TSV62x (420 kHz for 29 μA) for more power savings

Applications

- Battery-powered applications
- Portable devices
- Active filtering
- Medical instrumentation

Description

The TSV630 and TSV631 devices are single operational amplifiers offering low voltage, low power operation, and rail-to-rail input and output.

These devices have a very low input bias current and a low offset voltage making them ideal for applications that require precision. They can operate at power supplies ranging from 1.5 V to 5.5 V, and are therefore very suitable for batterypowered devices, extending battery life.

These op-amps feature an excellent speed/power consumption ratio, offering an 880 kHz gain bandwidth while consuming only 60 μ A at a 5 V supply voltage. They are unity gain stable for capacitive loads up to 100 pF.

The devices are internally adjusted to provide very narrow dispersion of AC and DC parameters. The TSV630 provides a shutdown function. Both devices are offered in micropackages and are guaranteed for industrial temperature ranges from -40° C to $+125^{\circ}$ C.

These features combined make the TSV630 and TSV631 ideal for sensor interfaces, batterysupplied and portable applications, as well as active filtering.

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This is information on a product in full production.

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Absolute maximum ratings and operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage ⁽¹⁾	6	
V _{id}	Differential input voltage ⁽²⁾	±V _{CC}	V
V _{in}	Input voltage ⁽³⁾	V _{CC-} -0.2 to V _{CC+} +0.2	
l _{in}	Input current ⁽⁴⁾	10	mA
SHDN	Shutdown voltage ⁽³⁾	6	V
T _{stg}	Storage temperature	-65 to +150	°C
R _{thja}	Thermal resistance junction to ambient ⁽⁵⁾⁽⁶⁾ SC70-6 SOT23-6 SC70-5 SOT23-5	232 240 205 250	°C/W
Тj	Maximum junction temperature	150	°C
	HBM: human body model ⁽⁷⁾	4	kV
ESD	MM: machine model ⁽⁸⁾	300	V
	CDM: charged device model ⁽⁹⁾	1.5	kV
	Latchup immunity	200	mA

Table 1. Absolute	maximum	ratings	(AMR)
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1. All voltage values, except the differential voltage, is with respect to network ground terminal.

- 2. The differential voltage is the non-inverting input terminal with respect to the inverting input terminal.
- 3. V_{CC} - V_{in} must not exceed 6 V.
- 4. Input current must be limited by a resistor in series with the inputs.
- 5. Short-circuits can cause excessive heating and destructive dissipation.
- 6. R_{th} are typical values.
- 7. Human body model: 100 pF discharged through a 1.5 k Ω resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
- Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω), done for all couples of pin combinations with other pins floating.
- 9. Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to the ground.

Table 2. O	Derating	conditions
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Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage	1.5 to 5.5	V
V _{icm}	Common mode input voltage range	V_{CC-} -0.1 to V_{CC+} +0.1	v
T _{oper}	Operating free air temperature range	-40 to +125	°C



2 Electrical characteristics

Table 3. Electrical characteristics at V_{CC+} = +1.8 V with V_{CC-} = 0 V, V_{icm} = V_{CC}/2, T_{amb} = 25 ° C and R_L connected to V_{CC}/2 (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
DC perfo	rmance						
		TSV630-TSV631 TSV630A-TSV631A			3 0.5		
V _{io}	Offset voltage	T _{min} < T _{op} < T _{max} TSV630-TSV631 TSV630A-TSV631A			4.5 2	mV	
DVio	Input offset voltage drift			2		μV/°C	
1	Input offset current			1	10 ⁽¹⁾		
I _{io}	$(V_{out} = V_{CC}/2)$	$T_{min} < T_{op} < T_{max}$		1	100	n A	
1	Input bias current			1	10 ⁽¹⁾	рА	
I _{ib}	$(V_{out} = V_{CC}/2)$	$T_{min} < T_{op} < T_{max}$		1	100		
CMR	Common mode rejection ratio	0 V to 1.8 V, V _{out} = 0.9 V	53	74		 I	
CIVIR	20 log ($\Delta V_{ic}/\Delta V_{io}$)	$T_{min} < T_{op} < T_{max}$	51			dB	
Δ.		R_L = 10 k Ω V _{out} = 0.5 V to 1.3 V	85	95		UD	
A _{vd}	Large signal voltage gain	$T_{min} < T_{op} < T_{max}$	80				
N/	High level output voltage	R _L = 10 kΩ	35	5			
V _{OH}	nigh level output voltage	$T_{min} < T_{op} < T_{max}$	50			m\/	
V.	Low level output voltage	R _L = 10 kΩ		4	35	mV	
V _{OL}		$T_{min} < T_{op} < T_{max}$			50		
	1	V _o = 1.8 V	6	12			
	lsink	$T_{min} < T_{op} < T_{max}$	4			mA	
I _{out}		V _o = 0 V	6	10			
	Isource	$T_{min} < T_{op} < T_{max}$	4				
1	Supply current	No load, V _{out} =V _{CC} /2	40	50	60	μA	
I _{CC}	SHDN = V _{CC+}	$T_{min} < T_{op} < T_{max}$			62	μΛ	
AC perfo	rmance						
GBP	Gain bandwidth product	R _L = 2 kΩ, C _L =100 pF, f= 100 kHz	700	790		kHz	
φm	Phase margin			48		Degrees	
G _m	Gain margin	- R _L = 2 kΩ, C _L = 100 pF		11		dB	
SR	Slew rate	$R_L = 2 k\Omega$, $C_L = 100 pF$, $Av = 1$	0.2	0.27		V/µs	
e _n	Equivalent input noise voltage	f = 1 kHz f = 10 kHz		67 53		<u>nV</u> √Hz	
				1	1	1	

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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit			
DC perfo	DC performance								
		SHDN = V _{CC-}		2.5	50	n۸			
I _{CC}	Supply current in shutdown mode (all operators)	T _{min} < T _{op} < 85° C			200	nA			
		T _{min} < T _{op} < 125° C			1.5	μA			
t _{on}	Amplifier turn-on time	$R_L = 2 k$, Vout = $V_{CC} + 0.2$ to $V_{CC} - 0.2$		300		20			
t _{off}	Amplifier turn-off time	$R_L = 2 \text{ k}$, Vout = $V_{CC-} + 0.2 \text{ to}$ $V_{CC+} - 0.2$		20		ns			
V _{IH}	SHDN logic high		1.3			V			
V _{IL}	SHDN logic low				0.5	v			
I _{IH}	SHDN current high	SHDN = V _{CC+}		10					
۱ _{IL}	SHDN current low	SHDN = V _{CC-}		10		pА			
	Output leakage in shutdown	SHDN = V _{CC-}		50					
l _{OLeak}	mode	T _{min} < T _{op} < 125° C		1		nA			

Table 4. Shutdown characteristics V_{CC} = 1.8 V



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perfor	mance				1	
		TSV630-TSV631 TSV630A-TSV631A			3 0.5	
V _{io}	Offset voltage	T _{min} < T _{op} < T _{max} TSV630-TSV631 TSV630A-TSV631A			4.5 2	mV
DVio	Input offset voltage drift			2		μV/°C
	Input offect ourrent			1	10 ⁽¹⁾	
I _{io}	Input offset current	$T_{min} < T_{op} < T_{max}$		1	100	
L.	Input bias current			1	10 ⁽¹⁾	рА
I _{ib}	input bias current	$T_{min} < T_{op} < T_{max}$		1	100	
CMR	Common mode rejection	0 V to 3.3 V, V_{out} = 1.75 V	57	79		
CIVITY	ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$)	$T_{min} < T_{op} < T_{max}$	53			dB
Δ.	Large signal voltage gain	R_L = 10 k Ω , V_{out} = 0.5 V to 2.8 V	88	98		UD
A _{vd}	Large signal voltage gain	$T_{min} < T_{op} < T_{max}$	83			
V _{OH}	High level output voltage	$R_L = 10 \ k\Omega$	35	6		
⊻ОН	Tight level output voltage	T _{min.} < T _{op} < T _{max}	50			mV
V _{OL}	Low level output voltage	$R_L = 10 k\Omega$		7	35	IIIV
♥ OL	Low level output voltage	$T_{min} < T_{op} < T_{max}$			50	
		V _o = 3.3 V	30	45		
Ι.	l _{sink}	$T_{min} < T_{op} < T_{max}$	25	42		mA
I _{out}		$V_0 = 0 V$	30	38		
	Isource	$T_{min} < T_{op} < T_{max}$	25			
laa	Supply current	No load, V _{out} = 1.75 V	43	55	64	μA
I _{CC}	SHDN = V _{CC+}	$T_{min} < T_{op} < T_{max}$			66	μπ
AC perfor	mance					
GBP	Gain bandwidth product	R _L = 2 kΩ, C _L = 100 pF, f = 100 kHz	710	860		kHz
φm	Phase margin	R ₁ = 2 kΩ, C ₁ = 100 pF		50		Degree
G _m	Gain margin			11		dB
SR	Slew rate	$R_L = 2 k\Omega, C_L = 100 \text{ pF}, \text{Av} = 1$	0.22	0.29		V/µs
e _n	Equivalent input noise voltage	f = 1 kHz f = 10 kHz		64 51		$\frac{nV}{\sqrt{Hz}}$

Table 5. Electrical characteristics at V_{CC+} = +3.3 V, V_{CC-} = 0 V, V_{icm} = V_{CC}/2, T_{amb} = 25 ° C, R_L connected to V_{CC}/2 (unless otherwise specified)

1. Guaranteed by design.



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perfor	mance					
		TSV630-TSV631 TSV630A-TSV631A			3 0.5	
V _{io}	Offset voltage	T _{min} < T _{op} < T _{max} TSV630-TSV631 TSV630A-TSV631A			4.5 2	mV
DVio	Input offset voltage drift			2		μV/°C
	Input offset current			1	10 ⁽¹⁾	
l _{io}	$(V_{out} = V_{CC}/2)$	T _{min} < T _{op} < T _{max}		1	100	
	Input bias current			1	10 ⁽¹⁾	рА
l _{ib}	$(V_{out} = V_{CC}/2)$	T _{min} < T _{op} < T _{max}		1	100	
CMD	Common mode rejection ratio	0 V to 5 V, V _{out} = 2.5 V	60	80		
CMR	$20 \log (\Delta V_{ic} / \Delta V_{io})$	T _{min} < T _{op} < T _{max}	55			
	Supply voltage rejection ratio	V _{CC} = 1.8 to 5 V	75	102		
SVR	20 log ($\Delta V_{CC} / \Delta V_{io}$)	T _{min} < T _{op} < T _{max}				dB
^	Large signal voltage gain	R _L = 10 kΩ, V _{out} = 0.5 V to 4.5 V	89	98		
A _{vd}	Large signal voltage gain	T _{min} < T _{op} < T _{max}	84			
M	High level output voltage	R _L = 10 kΩ	35	7		
V _{OH}		T _{min} < T _{op} < T _{max}	50			mV
V	Low level output voltage	R _L = 10 kΩ		6	35	111V
V _{OL}	Low level output voltage	$T_{min} < T_{op} < T_{max}$			50	
		$V_0 = 5 V$	40	69		
	l _{sink}	$T_{min} < T_{op} < T_{max}$	35	65		mA
l _{out}		$V_0 = 0 V$	40	74		
	Isource	$T_{min} < T_{op} < T_{max}$	36	68		
l	Supply current	No load, V _{out} =V _{CC} /2	50	60	69	μA
I _{CC}	SHDN = V _{CC+}	T _{min} < T _{op} < T _{max}			72	μΛ
AC perfor	mance					
GBP	Gain bandwidth product	$R_L = 2 k\Omega$, C _L = 100 pF, f = 100 kHz	730	880		kHz
Fu	Unity gain frequency			830		kHz
φm	Phase margin	R _L = 2 kΩ, C _L = 100 pF,		50		Degrees
G _m	Gain margin			12		dB
SR	Slew rate	$R_L = 2 k\Omega$, $C_L = 100 pF$, $Av = 1$	0.25	0.34		V/μs

Table 6. Electrical characteristics at V_{CC+} = +5 V with V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T_{amb} = 25° C and R_L connected to $V_{CC}/2$ (unless otherwise specified)



Table 6. Electrical characteristics at V_{CC+} = +5 V with V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T_{amb} = 25° C and R_L connected to $V_{CC}/2$ (unless otherwise specified) (continued)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
e _n	Equivalent input noise voltage	f = 1 kHz f = 10 kHz		60 47		$\frac{nV}{\sqrt{Hz}}$
THD+e _n	Total harmonic distortion	f = 1 kHz, A_V = 1, R_L = 100 kΩ, V_{icm} = $V_{CC}/2$, Vout = 2 V_{PP}		0.0017		%

1. Guaranteed by design.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit			
DC perform	DC performance								
		SHDN = V _{CC-}		5	50	5			
I _{CC}	Supply current in shutdown mode (all operators)	T _{min} < T _{op} < 85° C			200	nA			
		T _{min} < T _{op} < 125° C			1.5	μA			
t _{on}	Amplifier turn-on time	$R_L = 2 \text{ k}$, Vout = $V_{CC-} + 0.2 \text{ to}$ $V_{CC+} - 0.2$		300		20			
t _{off}	Amplifier turn-off time	$R_L = 2 \text{ k}$, Vout = $V_{CC-} + 0.2 \text{ to}$ $V_{CC+} - 0.2$		30		ns			
V _{IH}	SHDN logic high		4.5			V			
V _{IL}	SHDN logic low				0.5	v			
Ι _{ΙΗ}	SHDN current high	SHDN = V _{CC+}		10					
I _{IL}	SHDN current low	SHDN = V _{CC-}		10		pА			
1.	Output leakage in shutdown	SHDN = V _{CC-}		50					
l _{OLeak}	mode	T _{min} < T _{op} < 125° C		1		nA			

Table 7. Shutdown characteristics V_{CC} = 5 V



150

100

50

0

-50

-100

-150

1E7

Phase (°)

Phase

Figure 1. Supply current vs. supply voltage at $V_{icm} = V_{CC}/2$



 $V_{CC} = 5 V$

75

63

50

38

25

13

0

-13

-25

-38

-50 Sink

-75

40

20

0

-20

-40

Gain (dB)

Vid= -63

0.0 0.5 1.0

T=-40°C

1.5 2.0

Output Current (mA)



5.0

Figure 5. Voltage gain and phase vs. frequency

Output Voltage (V)

2.5 3.0 3.5

4.0 4.5



Figure 6. Phase margin vs. output current at $V_{CC} = 5 V$

Frequency (Hz)

100000

-40

10000

Gain

1000000





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Figure 2. Output current vs. output voltage at



Figure 7. Positive slew rate vs. time

Figure 8. Negative slew rate vs. time



Figure 9. Positive slew rate vs. supply voltage Figure 10. Negative slew rate vs. supply voltage



Figure 11. Distortion + noise vs. output voltage Figure 12. Distortion + noise vs. output voltage (R_L = 2 kΩ)

(R_L = 100 kΩ)





Vin=50mVpp

Vin=200mVpp

100

Vin=3Vpp

0.1

0.01

1E-3

10

THD + N (%)

Figure 13. Distortion + noise vs. frequency and input voltage

Vcc=5V

Gain=1

TIIII

1000

Frequency (Hz)

RI=2kOhms

BW=80kHz Vicm=Vcc/2

10000



Frequency (Hz)

Figure 14. Distortion + noise vs. frequency and output load resistor





3 Application information

3.1 Operating voltages

The TSV630 and TSV631 can operate from 1.5 V to 5.5 V. Their parameters are fully specified for 1.8-V, 3.3-V, and 5-V power supplies. However, the parameters are very stable in the full V_{CC} range and several characterization curves show the TSV63x characteristics at 1.5 V. Additionally, the main specifications are guaranteed in extended temperature ranges from -40° C to +125° C.

3.2 Rail-to-rail input

The TSV630 and TSV631 are built with two complementary PMOS and NMOS input differential pairs. The devices have a rail-to-rail input, and the input common mode range is extended from V_{CC-} -0.1 V to V_{CC+} +0.1 V. The transition between the two pairs appears at V_{CC+} -0.7 V. In the transition region, the performance of CMRR, PSRR, V_{io} and THD is slightly degraded (as shown in *Figure 16* and *Figure 17* for V_{io} vs. V_{icm}).

Figure 16. Input offset voltage vs input common Figure 17. Input offset voltage vs input common mode at V_{CC} = 1.5 V mode at V_{CC} = 5 V



The device is guaranteed without phase reversal.

3.3 Rail-to-rail output

The operational amplifiers' output levels can go close to the rails: to a maximum of 35 mV above and below the rail when a 10 k Ω resistive load is connected to V_{CC}/2.



3.4 Shutdown function (TSV630)

The operational amplifier is enabled when the \overline{SHDN} pin is pulled high. To disable the amplifier, the \overline{SHDN} must be pulled down to V_{CC-} . When in shutdown mode, the amplifier output is in a high impedance state. The \overline{SHDN} pin must never be left floating, but must be tied to V_{CC+} or V_{CC-} .

The turn-on and turn-off time are calculated for an output variation of ± 200 mV (*Figure 18* and *Figure 19* show the test configurations).

Figure 20 and *Figure 21* show the amplifier output voltage behavior when the SHDN pin is toggled high and low.









Figure 20. Turn-on time, $V_{CC} = \pm 2.5 V$, Vout pulled down, T = 25 ° C

Figure 21. Turn-off time, V_{CC} = ±2.5 V, Vout pulled down, T = 25 ° C



3.5 Optimization of DC and AC parameters

These devices use an innovative approach to reduce the spread of the main DC and AC parameters. An internal adjustment achieves a very narrow spread of the current consumption (60 μ A typical, min/max at ±17 %). Parameters linked to the current consumption value, such as GBP, SR and AVd, benefit from this narrow dispersion. All parts present a similar speed and the same behavior in terms of stability. In addition, the minimum values of GBP and SR are guaranteed (GBP = 730 kHz minimum and SR = 0.25 V/µs minimum).

3.6 Driving resistive and capacitive loads

These products are micro-power, low-voltage operational amplifiers optimized to drive rather large resistive loads, above 2 k Ω For lower resistive loads, the THD level may significantly increase.

In a *follower* configuration, these operational amplifiers can drive capacitive loads up to 100 pF with no oscillations. When driving larger capacitive loads, adding an in-series resistor at the output can improve the stability of the devices (see *Figure 22* for recommended in-series resistor values). Once the in-series resistor value has been selected, the stability of the circuit should be tested on the bench and simulated with the simulation model.



Figure 22. In-series resistor vs. capacitive load

3.7 PCB layouts

For correct operation, it is advised to add 10 nF decoupling capacitors as close as possible to the power supply pins.



3.8 Macromodel

An accurate macromodel of the TSV630 and TSV631 is available on STMicroelectronics' web site at www.st.com. This model is a trade-off between accuracy and complexity (that is, time simulation) of the TSV63x operational amplifiers. It emulates the nominal performances of a typical device within the specified operating conditions mentioned in the datasheet. It also helps to validate a design approach and to select the right operational amplifier, *but it does not replace on-board measurements*.



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.



4.1 SC70-6 (or SOT323-6) package mechanical data



Figure 23. SC70-6 (or SOT323-6) package mechanical drawing

Table 8. SC70-6 (or SOT323-6) package mechanical data

	Dimensions							
Ref		Millimeters		Inches				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
А	0.80		1.10	0.031		0.043		
A1			0.10			0.004		
A2	0.80		1.00	0.031		0.039		
b	0.15		0.30	0.006		0.012		
С	0.10		0.18	0.004		0.007		
D	1.80		2.20	0.071		0.086		
E	1.15		1.35	0.045		0.053		
е		0.65			0.026			
HE	1.80		2.40	0.071		0.094		
L	0.10		0.40	0.004		0.016		
Q1	0.10		0.40	0.004		0.016		



Figure 24. SC70-6 (or SOT323-6) package footprint



4.2 SOT23-6 package mechanical data





Table 9. SOT23-6 package mechanical data

	Dimensions					
Ref.		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	0.90		1.45	0.035		0.057
A1			0.10			0.004
A2	0.90		1.30	0.035		0.051
b	0.35		0.50	0.013		0.019
С	0.09		0.20	0.003		0.008
D	2.80		3.05	0.110		0.120
Е	1.50		1.75	0.060		0.069
е		0.95			0.037	
Н	2.60		3.00	0.102		0.118
L	0.10		0.60	0.004		0.024
θ	0 °		10 °	0 °		10 °



4.3 SC70-5 (or SOT323-5) package mechanical data



Figure 26. SC70-5 (or SOT323-5) package mechanical drawing

Figure 27. SC70-5 (or SOT323-5) package mechanical data

	Dimensions						
Ref	Millimeters			Inches			
	Min	Тур	Мах	Min	Тур	Мах	
А	0.80		1.10	0.315		0.043	
A1			0.10			0.004	
A2	0.80	0.90	1.00	0.315	0.035	0.039	
b	0.15		0.30	0.006		0.012	
С	0.10		0.22	0.004		0.009	
D	1.80	2.00	2.20	0.071	0.079	0.087	
E	1.80	2.10	2.40	0.071	0.083	0.094	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65			0.025		
e1		1.30			0.051		
L	0.26	0.36	0.46	0.010	0.014	0.018	
<	0°		8°				

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4.4 SOT23-5 package mechanical data



Figure 28. SOT23-5 package mechanical drawing

	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	0.90	1.20	1.45	0.035	0.047	0.057
A1			0.15			0.006
A2	0.90	1.05	1.30	0.035	0.041	0.051
В	0.35	0.40	0.50	0.013	0.015	0.019
С	0.09	0.15	0.20	0.003	0.006	0.008
D	2.80	2.90	3.00	0.110	0.114	0.118
D1		1.90			0.075	
е		0.95			0.037	
E	2.60	2.80	3.00	0.102	0.110	0.118
F	1.50	1.60	1.75	0.059	0.063	0.069
L	0.10	0.35	0.60	0.004	0.013	0.023
К	0 °		10 °	0 °		10 °

Table 10. SOT23-5 package mechanical data



5 Ordering information

Order code	Temperature range	Package	Packing	Marking
TSV630ILT		SOT23-6		K108
TSV630ICT		SC70-6		K18
TSV631ILT		SOT23-5		K109
TSV631ICT	-40°C to +125°C	SC70-5	Tape and reel	K19
TSV631IYLT ⁽¹⁾		SOT23-5		K10C
TSV630AILT		SOT23-6		K141
TSV630AICT		SC70-6		K41
TSV631AILT		SOT23-5		K142
TSV631AICT		SC70-5		K42

Table 11. Order codes

1. Qualified and characterized according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 and Q002 or equivalent.

6 Revision history

Date	Revision	Changes
19-Dec-2008	1	Initial release.
17-Aug-2009	2	Added root part numbers TSV630A and TSV631A on cover page.
13-Aug-2012	3	 Corrected the "Equivalent input noise voltage" values in <i>Table 3, 5</i> and 6. Updated <i>Figure 15: Noise vs. frequency</i>.
22-Mar-2013 4		<i>Features</i> : added "automotive qualification" Added <i>Related products</i> <i>Description</i> : updated Updated titles of <i>Figure 13</i> and <i>Figure 14</i> . Updated <i>Section 3.4: Shutdown function (TSV630)</i> . Updated <i>Table 11: Order codes</i> .



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